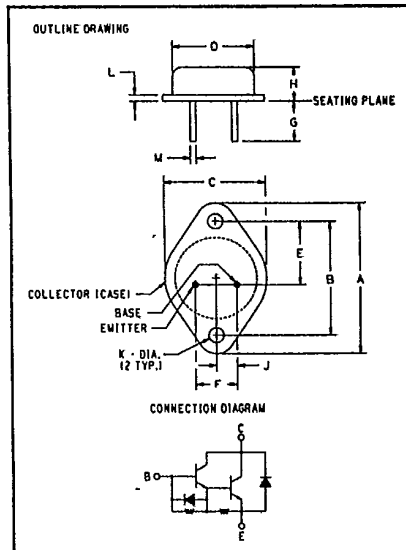
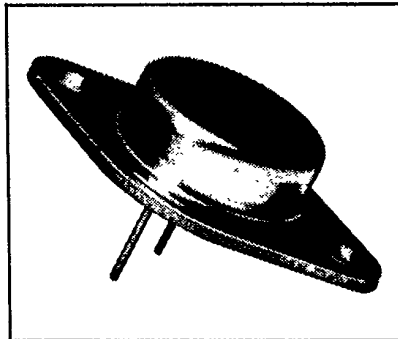


**POWEREX****D64EV**

Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

**Fast Switching  
Single Darlington  
Transistor Module****50 Amperes****500-600-700 Volts****500-600-700 Volts D64EV  
Outline Drawing**

Dimension	Inches	Millimeters
A	1.573 Max.	39.96
B	1.187 ± .010	30 ± 0.15
C	1.050 Max.	26.68 Max.
D	.845 Dia.	21.47 Dia.
E	.662 ± .012	18.8 ± 0.3
F	.430 ± .005	11 ± 0.12
G	.426 Min.	10.82 Min.
H	.358 Max.	9.1 Max.
J	.215 ± .005	5.5 ± 0.12
K	.156 ± .006 Dia.	4 ± 0.15 Dia.
L	.065 Max.	1.65 Max.
M	.060 ± .003 Dia.	1.5 ± 0.08 Dia.

**D64EV  
Fast Switching Single Darlington  
Transistor Module**  
50 Amperes/500-600-700 Volts**Description**

Powerex Fast Switching Single Darlington Transistor Modules are designed for use in switching applications.

**Features:**

- High Speed
- High Gain ( $h_{FE}$ )
- Base Emitter Speed-up Diode

**Applications:**

- UPS Inverters
- DC Motor Control
- Switching Power Supplies
- AC Motor Control
- HF Power Conversion

**Ordering Information**

Example: Select the complete six digit module part number for the rating you desire from the table - i.e. D64EV7 is a 700 Volt, 50 Ampere Fast Switching Single Darlington Module with speed-up diode.

Type	V <sub>CEV(SUS)</sub> Volts (×100)	Current Rating Amperes (50)
D64EV	5	50
D64EV	6	50
D64EV	7	50



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**D64EV**  
Fast Switching Single Darlington Transistor Module  
50 Amperes/500-800-700 Volts

**Maximum Ratings  $T_J = 25^\circ\text{C}$  unless otherwise specified**

	Symbol	D64EV	Units
Junction Temperature	$T_J$	-65 to 150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-65 to 150	$^\circ\text{C}$
Collector-Emitter Sustaining Voltage D64EV5	$V_{CE(SUS)}$	400	Volts
Collector-Base Voltage D64EV5	$V_{CBO}$	500	Volts
Collector-Emitter Sustaining Voltage D64EV6	$V_{CE(SUS)}$	450	Volts
Collector-Base Voltage D64EV6	$V_{CBO}$	600	Volts
Collector-Emitter Sustaining Voltage D64EV7	$V_{CE(SUS)}$	500	Volts
Collector-Base Voltage D64EV7	$V_{CBO}$	700	Volts
Emitter-Base Voltage	$V_{EBO}$	5	Volts
Continuous Collector Current	$I_C$	50	Amperes
Peak (Repetitive) Collector Current	$I_{CM}$	75	Amperes
Peak (Non-Repetitive) Collector Current	$I_{CSM}$	125	Amperes
Diode Forward Current	$I_{FM}$	50	Amperes
Continuous Base Current	$I_B$	10	Amperes
Peak (Non-Repetitive) Base Current	$I_{BM}$	20	Amperes
Power Dissipation	$P_T$	180	Watts

**Electrical and Mechanical Characteristics  $T_J = 25^\circ\text{C}$  unless otherwise specified**

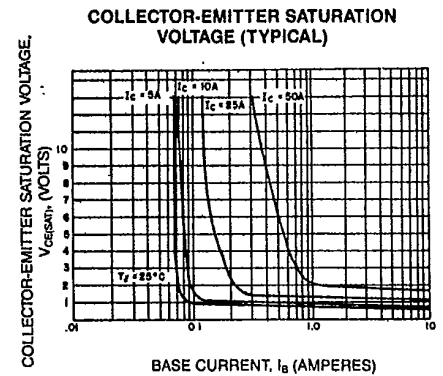
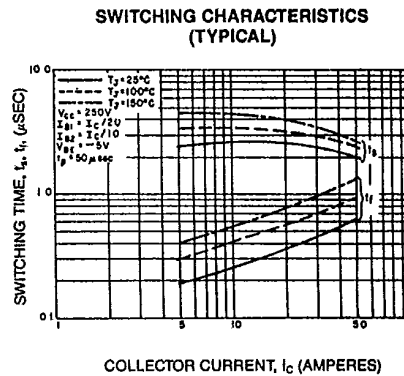
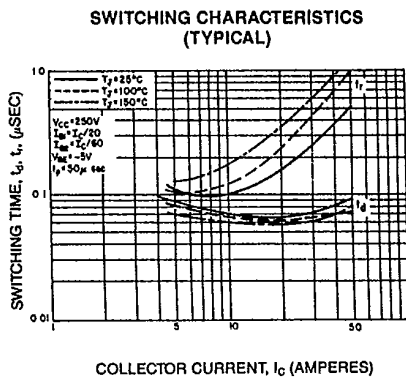
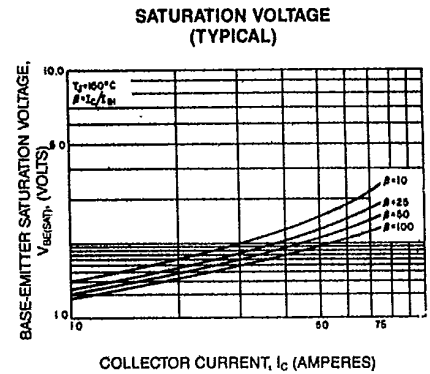
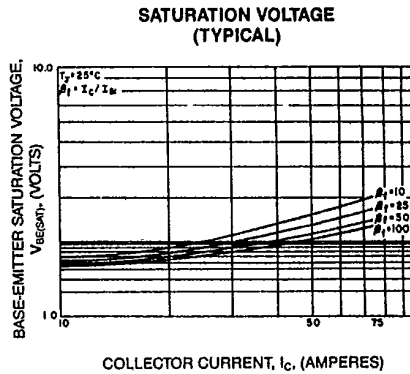
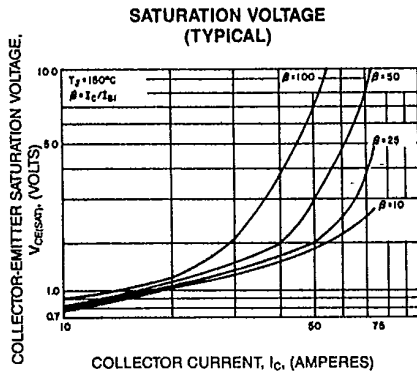
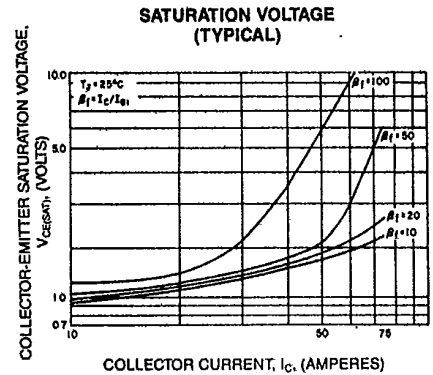
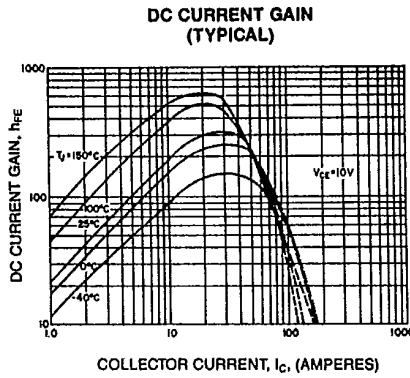
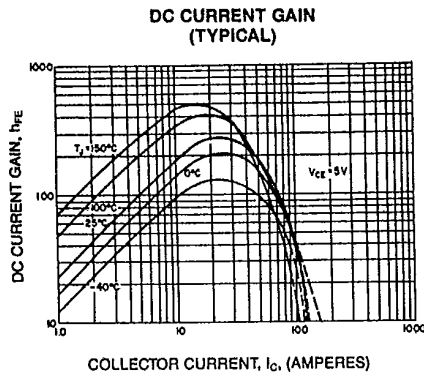
Characteristics	Symbol	Test Conditions	Min.	D64EV Typ.	Max.	Units
Collector Cutoff Current	$I_{CEV}$	$V_{CE} = V_{CE}(\text{rated}), V_{BE} = -1.5\text{V}$	—	—	1	mA
Collector Cutoff Current	$I_{CEV}$	$V_{CE} = V_{CE}(\text{rated}), V_{BE} = -1.5\text{V}$ $T_C = 150^\circ\text{C}$	—	—	2.5	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 1.5\text{V}$	—	—	350	mA
DC Current Gain	$h_{FE}$	$I_C = 75\text{A}, V_{CE} = 5.0\text{V}$ $I_C = 50\text{A}, V_{CE} = 5.0\text{V}$ $I_C = 20\text{A}, V_{CE} = 5.0\text{V}$	25 50 100	60 135 250	— — —	— — —
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 75\text{A}, I_B = 5.0\text{A}$ $I_C = 50\text{A}, I_B = 4.0\text{A}$ $I_C = 20\text{A}, I_B = 2.0\text{A}$	— — —	2.2 1.7 1.15	3.0 2.0 1.5	V V V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 75\text{A}, I_B = 5.0\text{A}$ $I_C = 50\text{A}, I_B = 4.0\text{A}$ $I_C = 20\text{A}, I_B = 2.0\text{A}$	— — —	2.8 2.45 1.95	3.5 3.0 2.5	V V V
Delay Time*	$t_d$	—	—	0.09	0.5	$\mu\text{s}$
Rise Time*	$t_r$	$V_{CC} = 250\text{V}, I_C = 50\text{A}$	—	0.5	1.0	$\mu\text{s}$
Storage Time*	$t_s$	$I_{B1} = 2.5\text{A}, -I_{B2} = 5\text{A}$	—	2.0	3.0	$\mu\text{s}$
Fall Time*	$t_f$	$t_p = 50 \mu\text{sec}$	—	.64	1.0	$\mu\text{s}$
Diode Power Dissipation	$P_D$	$I_{B1} = 0$	—	—	125	W
Diode Forward Voltage	$V_{FM}$	$I_{FM} = 25\text{A}$ $I_{FM} = 50\text{A}$ $I_{FM} = 50\text{A}, T_J = 150^\circ\text{C}$	— — —	1.95 2.6 2.3	3.20 3.80 3.50	V V V
Reverse Recovery Time	$t_{rr}$	$I_{FM} = 50\text{A}, di/dt = 25\text{A}/\mu\text{sec}$ $R_{B1E} = .25\Omega$	—	3.85	10.0	$\mu\text{s}$
Forward Turn-On Time	$t_{ON}$	$I_{FM} = 100\text{A}, di/dt = 100\text{A}/\mu\text{sec}$	—	0.75	1.5	$\mu\text{s}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	Transistor Part	—	—	.7	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	Diode Part	—	—	1.0	$^\circ\text{C}/\text{W}$
Max Lead Temp for Soldering	$T_L$	1/8" From case for 5 sec.	—	—	300	$^\circ\text{C}$

\*Resistive Load.



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**D64EV**  
Fast Switching Single Darlington Transistor Module  
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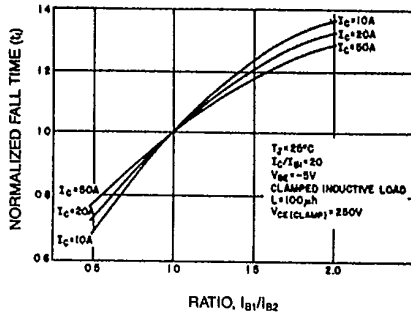




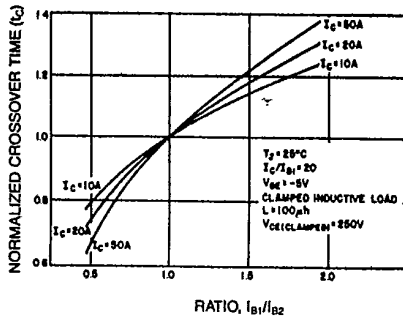
Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

D64EV  
Fast Switching Single Darlingtion Transistor Module  
50 Amperes/500-600-700 Volts

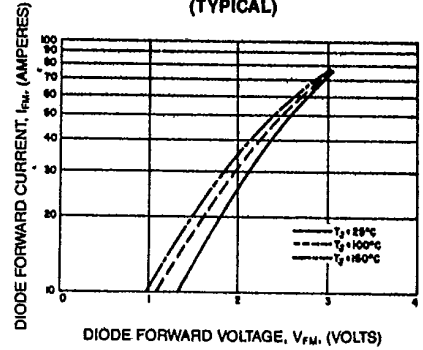
SWITCHING TIME VS. BASE CURRENT (TYPICAL)



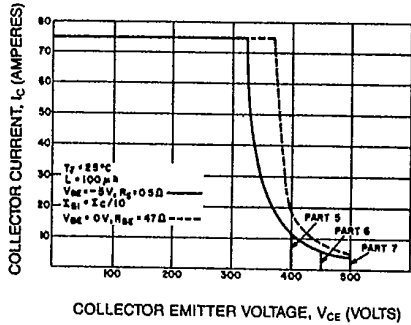
SWITCHING TIME VS. BASE CURRENT (TYPICAL)



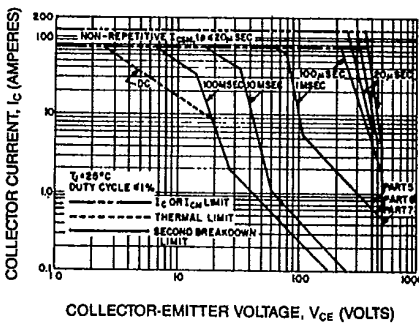
DIODE CHARACTERISTICS (TYPICAL)



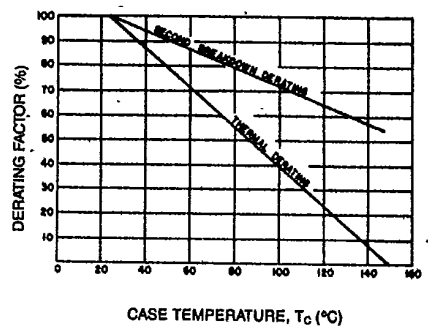
REVERSE BIAS SAFE OPERATING AREA (R.B.S.O.A.)



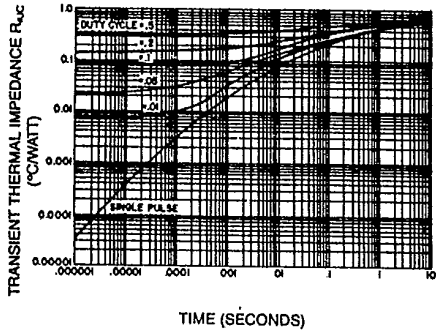
FORWARD BIAS SAFE OPERATING AREA (S.O.A.)



DERATING FACTOR OF SAFE OPERATING AREA (S.O.A.)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (TRANSISTOR)



Switching Time Test Circuit

